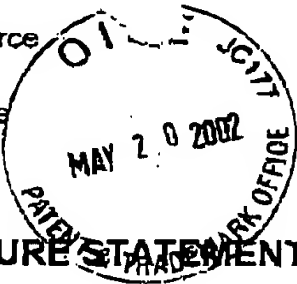


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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Atty. Dkt. No.	M#	Client Ref.
	273686	F00-219-US-DIV-3

Applicant: MANABE et al.

Appln. No.: 09/677,781

Filing Date: October 2, 2000

Examiner: S. MULPURI

Group Art Unit: 2812

Date: May 20, 2002

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	CR					
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	ER					

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Sm	FR	58-200527	11/1983	Japan			X			
Sm	GR	60-175468	09/1985	Japan			X			
Sm	HR	63-188938	08/1988	Japan			X			
Sm	IR	02-042770	02/1990	Japan			X			
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	RR	SZE, S., "Physics of Semiconductor Devices," <i>Wiley-Interscience</i> , 1969, pp. 42-43.			
Sm	SR	TIETJEN, J., "Vapor Phase Growth Technique and System for Several III-V Compound Semiconductors," <i>RCA Laboratories</i> , 1969, pp. 1-8.			DUPLICATE
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	UR				
	VR				
	WR				

Examiner

S. Mulpuri

Date Considered:

9/29/02

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GM	TR	Jacob et al., <i>Efficient Injection Mechanism for Electroluminescence in GaN</i> , Applied Physics Letter, Vol. 30, No. 8, pp. 412-414, April 15, 1977			
GM	UR	Tietjen et al., <i>Vapor Phase Growth Technique and System for Several III-V Compound Semiconductors</i> , RCA Laboratories, 5 pages, March 1969		X	Partial
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Examiner: *S. Mulpuri* Date Considered: *12/9/03*

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Div. of Appln. No.: 09/417,778

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Examiner: Minh Loan Tran Group Art Unit: 2811

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		Document Number	Date MM/YYYY	Country	Inventor Name	Class	SubClass	Enclosed	No	Enclose	No
SM	OR	2-229475	09/1990	Japan					X		X
	PR	2-275682	11/1990	Japan					X		X
	QR	5-042785	04/1975	Japan					X		X
	RR	59-228776	12/1994	Japan					X		X
	SR	0 620 203 A1	10/1994	Europe	Nakahata				X		X
	TR	0-277597	08/1988	EPA					X		X
	UR	03-034549	02/1991	Japan	Toyoda				X		X
	VR	34549	02/1991	Japan	Hatano				X		X
	WR	4,006,449	09/1990	Germany	Manabe				X		X
SM	XR	57-018377	01/1982	Japan	KOBAYASHI				X		X

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	NR	61-007671	01/1986	Japan	Kawabata				x		x
	OR	57-087184	05/1982	Japan	Tabuchi				x		x
	PR	57-153479	09/1982	Japan	Ooki				x		x
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	RR	56-59699	05/1981	Japan	Ooki				x		x
	SR	34549	02/1991	Japan	Hatano				x		x
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	WR	Bottka, et al., Silicon and beryllium doping of OMVPE Grown..., Journal of Crystal Growth 68 (1984) pp. 54-59, North-Holland Amsterdam									
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Group Art Unit: 2811

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							Enclosed	No	Enclose	No
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	OR 59-228776	6/1983	Japan	Maefutsu et al.				X		X
	PR 60-173829	2/1984	Japan	Maefutsu et al.				X		X
	QR 1-589351	05/1981	England							
	RR 63-188977	08/1988	Japan							
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	TR 57-046669	10/1982	Japan							
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SM	VR 54-071589	06/1979	Japan	Toyoda						

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	XR	I. Akusuki et al., "Effects of AlN Buffer Layer on Crystallographic Structure... by MOVPE", J. Crystal Growth 98 (1989) pp. 209-19.								
	YR	Sayyah, A Study of Growth Mechanisms and Electrical and Optical Properties of Epitaxial Al _x Ga _{1-x} N Layers Grown by Atmospheric Pressure Metalorganic Chemical Vapor Deposition, A Dissertation presented to Faculty of the Graduate School, University of Southern California, February 1986, pp. 125-136.								
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	NR	54-071590	06/1979	Japan	Toyoda				X		X
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	PR	02-081483	03/1990	Japan	Manabe				X		X
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XR	A.S. Grove, Physics and Technology of Semiconductor, Chapter 4: Basics of Semiconductor Physics, 1967, translated and published in Japan June 23, 1995, pp. 112-123.				

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